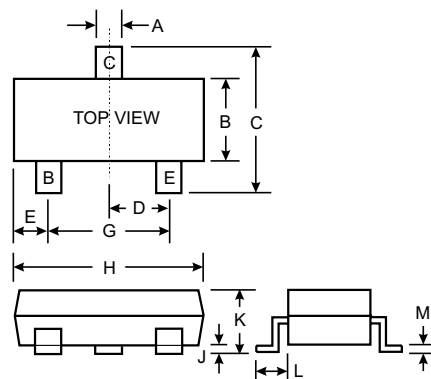


Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMSTA63/MMSTA64)
- Ideal for Medium Power Amplification and Switching
- High Current Gain
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-323, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- MMSTA13 Marking K2D, K3D
- MMSTA14 Marking K3D
- Weight: 0.006 grams (approx.)



SOT-323		
Dim	Min	Max
A	0.30	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMSTA13	MMSTA14	Unit
Collector-Base Voltage	V_{CBO}	30		V
Collector-Emitter Voltage	V_{CEO}	30		V
Emitter-Base Voltage	V_{EBO}	10		V
Collector Current - Continuous (Note 1)	I_C	300		mA
Power Dissipation (Note 1)	P_d	200		mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625		K/W
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150		$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30	—	V	$I_C = 100\mu\text{A}, V_{BE} = 0\text{V}$
Collector Cutoff Current	I_{CBO}	—	100	nA	$V_{CB} = 30\text{V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}	—	100	nA	$V_{EB} = 10\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	5,000 10,000 10,000 20,000	—	—	$I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	1.5	V	$I_C = 100\text{mA}, I_B = 100\mu\text{A}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	—	2.0	V	$I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	8.0 Typical		pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	15 Typical		pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	125	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$

- Notes:
1. Valid provided that terminals are kept at ambient temperature.
 2. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.